# N-Channel 40-V (D-S) MOSFET

## Key Features:

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

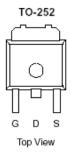
### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY |                             |       |  |  |
|-----------------|-----------------------------|-------|--|--|
| VDS (V)         | $r_{DS(on)}(m\Omega)$       | I⊳(A) |  |  |
| 40              | 32 @ V <sub>GS</sub> = 10V  | 33    |  |  |
|                 | 42 @ V <sub>GS</sub> = 4.5V | 29    |  |  |

in l





| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED) |                      |                                   |            |       |  |
|---|----------------------|-----------------------------------|------------|-------|--|
| Parameter   |                      |                                   | Limit      | Units |  |
| Drain-Source Voltage  |                      |                                   | 40         | V     |  |
| Gate-Source Voltage   | V <sub>GS</sub>      | ±20                               | v          |       |  |
| Continuous Drain Current <sup>a</sup>                                   | T <sub>A</sub> =25°C | I <sub>D</sub>                    | 33 A       |       |  |
| Pulsed Drain Current <sup>b</sup>                                       |                      | I <sub>DM</sub>                   | 50         | ~     |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>               |                      | ا <sub>s</sub>                    | 35         | А     |  |
| Power Dissipation <sup>a</sup>  | T <sub>A</sub> =25°C | PD                                | 50         | W     |  |
| Operating Junction and Storage Temperature Range                        |                      | T <sub>J</sub> , T <sub>stg</sub> | -55 to 175 | °C    |  |

| THERMAL RESISTANCE RATINGS               |                       |         |       |  |  |
|--|-----------------------|---------|-------|--|--|
| Parameter                                | Symbol                | Maximum | Units |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{	extsf{	heta}JA}$ | 40      | °C/W  |  |  |
| Maximum Junction-to-Case                 | $R_{	extsf{	heta}JC}$ | 3       | C/ VV |  |  |

Notes

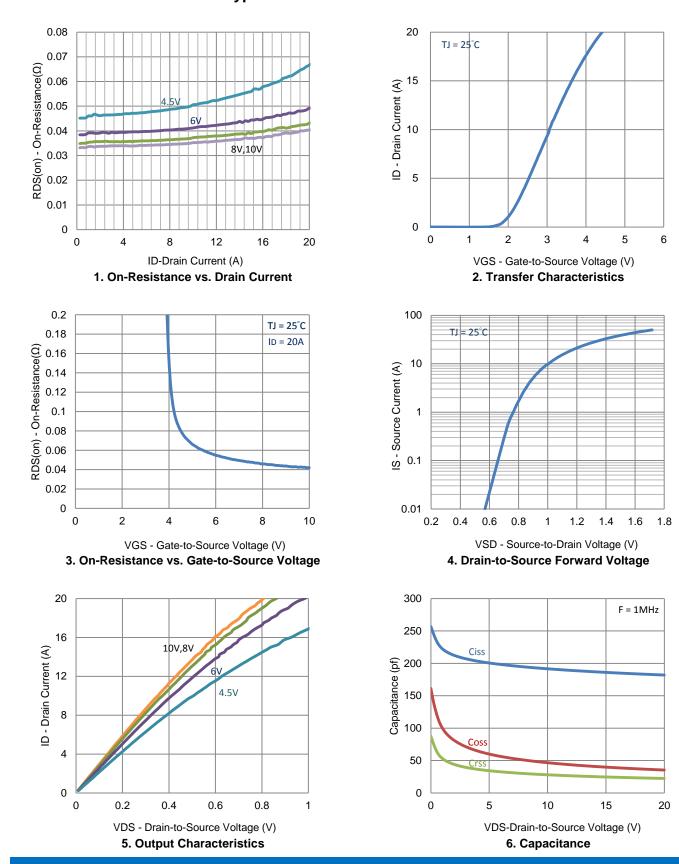
- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

| Parameter                       | Symbol                 | nbol Test Conditions  |    | Тур  | Мах  | Unit  |  |
|---------------------------------|------------------------|---|----|------|------|-------|--|
| Static                          |                        |   |    |      |      |       |  |
| Gate-Source Threshold Voltage   | V <sub>GS(th)</sub>    | $V_{DS} = V_{GS}, I_D = 250 \text{ uA}$                                   | 1  |      |      | V     |  |
| Gate-Body Leakage               | I <sub>GSS</sub>       |   |    |      | ±100 | nA    |  |
| Zero Gate Voltage Drain Current | Inco                   | $V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}$                             |    |      | 1    |       |  |
| Zero Gale Voltage Drain Current | IDSS                   | $V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ |    |      | 25   | – uA  |  |
| On-State Drain Current          | I <sub>D(on)</sub>     | $V_{DS} = 5 V, V_{GS} = 10 V$   | 33 |      |      | А     |  |
| Drain-Source On-Resistance      | r.                     | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$                     |    |      | 32   | mΩ    |  |
| Drain-Source On-Resistance      | r <sub>DS(on)</sub>    | $V_{GS} = 4.5 \text{ V}, I_{D} = 18 \text{ A}$                            |    |      | 40   | 11152 |  |
| Forward Transconductance        | <b>g</b> <sub>fs</sub> | $V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$                     |    | 10   |      | S     |  |
| Diode Forward Voltage           | $V_{SD}$               | I <sub>S</sub> = 17.6 A, V <sub>GS</sub> = 0 V                            |    | 1.15 |      | V     |  |
|                                 |                        | Dynamic   |    |      |      |       |  |
| Total Gate Charge               | Q <sub>g</sub>         | $V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 5.5 \text{ V},$                  |    | 3    |      | nC    |  |
| Gate-Source Charge              | $Q_gs$                 | $V_{\rm DS} = 20$ V, $V_{\rm GS} = 3.3$ V,<br>$I_{\rm D} = 20$ A          |    | 1.7  |      |       |  |
| Gate-Drain Charge               | $Q_gd$                 | 10 - 20 A   |    | 1.0  |      |       |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>     | $V_{DS} = 20 \text{ V}, \text{ R}_{L} = 1 \Omega,$                        |    | 2    |      |       |  |
| Rise Time                       | t <sub>r</sub>         | $v_{\rm DS} = 20  v_1  R_L - 1  \Omega_2,$<br>$I_{\rm D} = 20  \rm A,$    |    | 4    |      | 200   |  |
| Turn-Off Delay Time             | t <sub>d(off)</sub>    | $V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$        |    | 10   |      | ns    |  |
| Fall Time                       | t <sub>f</sub>         | $v_{\text{GEN}} = 10 v, 1 v_{\text{GEN}} = 0.02$                          |    | 4    |      |       |  |
| Input Capacitance               | C <sub>iss</sub>       |   |    | 186  |      |       |  |
| Output Capacitance              | C <sub>oss</sub>       | $V_{DS}$ = 15 V, $V_{GS}$ = 0 V, f = 1 MHz                                |    | 40   |      | pF    |  |
| Reverse Transfer Capacitance    | C <sub>rss</sub>       |   |    | 25   |      |       |  |

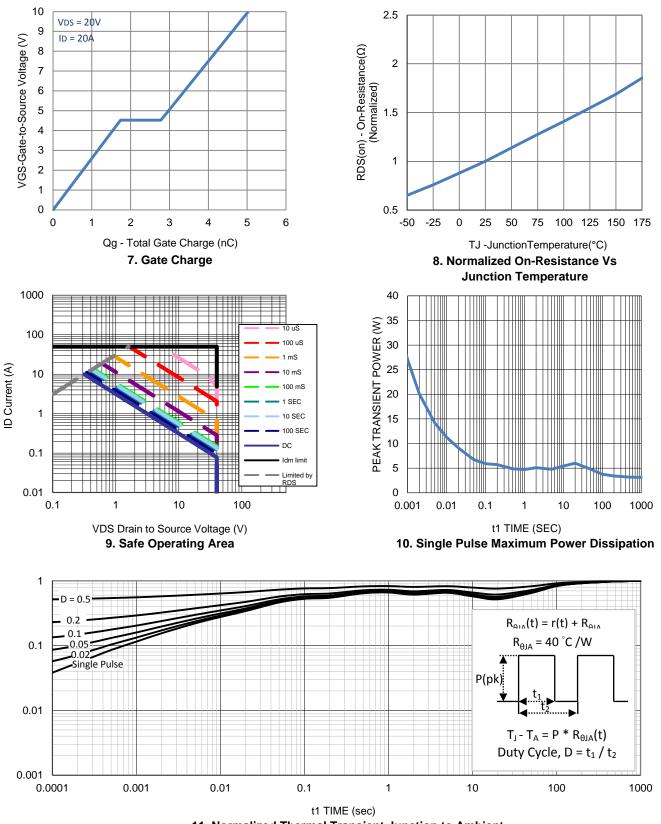
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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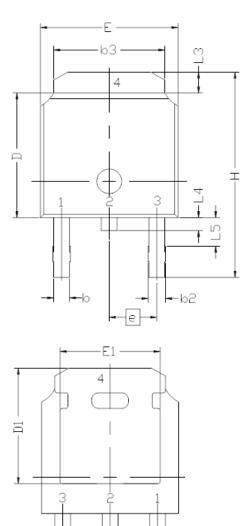
## **Typical Electrical Characteristics**



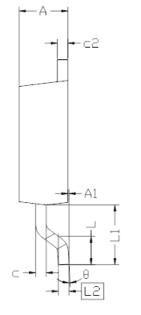
## **Typical Electrical Characteristics**

11. Normalized Thermal Transient Junction to Ambient

## **Package Information**



SINGLE ROWNEW



|        | DIMENS | IONAL F | REQMTS |
|--------|--------|---------|--------|
| SYMBOL | MIN    | NDM     | MAX    |
| E      | 6.40   | 6.60    | 6.731  |
| L      | 1.40   | 1.52    | 1.77   |
| L1     |        | .743 RI |        |
| L2     | 0.     | 508 BS  |        |
| L3     | 0.89   |         | 1.27   |
| L4     | 0.64   |         | 1.01   |
| L5     |        |         |        |
| D      | 6.00   | 6.10    | 6.223  |
| Н      | 9.40   | 10.00   | 10.40  |
| b      | 0.64   | 0.76    | 0.88   |
| b2     | 0.77   | 0.84    | 1.14   |
| b3     | 5.21   | 5.34    | 5.46   |
| e      |        | 286 BS  |        |
| A      | 2.20   | 2.30    | 2.38   |
| A1     | 0      |         | 0.127  |
| C      | 0.45   | 0.50    | 0.60   |
| c2     | 0.45   | 0.50    | 0,58   |
| D1     | 5.30   |         |        |
| E1     | 4.40   |         |        |
| θ      | 0°     |         | 10°    |

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.